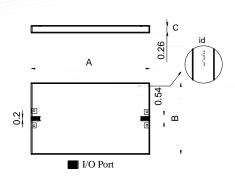
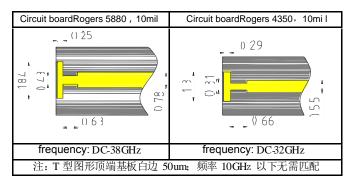


Thin Film ceramic Filte BMBP22R15/2R7-6PA

Precautions

- 1. The chip is recommended sub-cavity use, both sides of the side wall from about 0.2mm, surface distance Cover about 3mm, the chip ports are interchangeable;
- 2. Chip recommended low-stress conductive adhesive (such as ME8456) bonding:
- 3. Chip should be installed in Kovar (recommended) or molybdenum copper with ceramic thermal expansion coefficient(6.7ppm / $^{\circ}$ C) on the carrier, the carrier thickness \geq 0.2mm;
- 4 circuit board micro-chip wire bonding connection, it is recommended microstrip bonding at mining T-type structure to match, T-size as right





Features

high-precision film processing technology	
high performance, low temperature drift, high power	
Ceramic substrate, 50Ω coplanar waveguide output	
Gold wire bonding, suitable for multi-chip integrated module applications	

Environmental parameters

Working temperature	-55°C~+85°C
storage temperature	-55°C~+125°C
Maximum input power	35dBm

Electrical Specifications

Center frequency(f0)	22.15
Passband frequency range (GHz)	20.9-23.2
Band fluctuations (dB)	1
Center insertion loss (dB)	2.5
Return loss (dB)	13
Band attenuation (dB)	≥ 40@ 19.6 GHz ≥ 40@2 5.0 GHz

